

ABSTRACT OF THE DISCLOSURE

ETCHING SOLUTION FOR SELECTIVELY REMOVING SILICON-GERMANIUM ALLOY FROM A SILICON-GERMANIUM/ GERMANIUM STACK DURING MANUFACTURE OF A SEMICONDUCTOR DEVICE

Described herein is an etching solution comprising water; an oxidizer; a water-miscible organic solvent; a fluoride ion source; a corrosion inhibitor and optionally, a surfactant, optionally a buffer, optionally a chelating agent. Such compositions are useful for the selective removal of silicon-germanium over germanium from a microelectronic device having such material(s) thereon during its manufacture.

FIG. 1